



For immediate release

Diodes Incorporated Introduces a Dual MOSFET Combination that Saves Space without Compromising Performance

Dallas, Texas – May 27, 2009 – Diodes Incorporated (Nasdaq: DIOD), a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete and analog semiconductor markets, today introduced a complementary pair of 100V enhancement mode MOSFETs in an SO8 package that achieves the same performance as that of much larger individually packaged parts. The ZXMC10A816 is aimed at H-bridge circuits in DC fan and inverter circuits, Class D amplifier output stages, and an array of 48V applications.

Enabling designers to replace equivalent devices in SOT223 and DPak (TO252) packages, the N- and P-channel MOSFET combination reduces board space and component count as well as simplifies gate drive circuit layouts. As an illustration of its space saving potential, the SO8 package's footprint of just 31mm² is only 30% that of two SOT223 MOSFETs.

The N- and P-channel MOSFETs used in the dual device package exhibit low gate charge and typical $R_{DS(ON)}$ of 230m Ω and 235m Ω , respectively, at V_{GS} of 10V, ensuring that switching and on-state losses are minimized. Both 2.4W and 2.6W are respective power dissipation figures.

About Diodes Incorporated

Diodes Incorporated (Nasdaq: DIOD), a Standard & Poor's SmallCap 600 and Russell 3000 Index company, is a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete and analog semiconductor markets, serving the consumer electronics, computing, communications, industrial and automotive markets. Diodes' products include diodes, rectifiers, transistors, MOSFETs, protection devices, functional specific arrays, amplifiers and comparators, Hall-effect sensors and temperature sensors, power management devices including LED drivers, DC-DC switching regulators, linear voltage regulators and voltage references, along with special function devices including USB power switch, load switch, voltage supervisor and motor controllers. The Company's corporate headquarters are located in Dallas, Texas. A sales, marketing, engineering and logistics office is located in Westlake Village, California. Design centers are located in Dallas; San Jose, California; Taipei, Taiwan; Manchester, England and Neuhaus, Germany. The Company's wafer fabrication facilities are located in Kansas City, Missouri and Manchester; with two manufacturing facilities located in Shanghai, China, another in Neuhaus, and a joint venture facility located in Chengdu, China. Additional engineering, sales, warehouse and logistics offices are located in Taipei; Hong Kong; Manchester and Munich, Germany,

with support offices located throughout the world. For further information, including SEC filings, visit the Company's website at <http://www.diodes.com>.

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